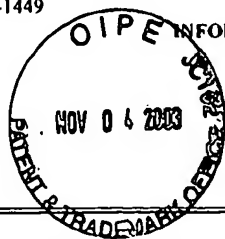


Form PTO-1449



**INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)

068758.0102

Application Number

09786,022
10/633,044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
Ps	3,171,068	02/23/65	Denkwalter et al.	317	234	10/19/60
	3,925,803	12/09/75	Kobayashi	357	22	07/12/73
	3,961,356	06/01/76	Okuhara et al.	357	50	10/31/74
	4,003,072	01/11/77	Matsushita et al.	357	52	11/01/74
	4,055,884	11/01/77	Jambotkar	29	571	12/13/76
	4,072,975	02/07/78	Ishtiani	357	23	04/22/77
	4,101,922	07/18/78	Tihanyi	357	23	03/09/77
	4,145,700	03/20/79	Jambotkar	357	23	08/08/77
	4,320,410	03/16/82	Nishizawa et al.	357	43	05/03/79
	4,345,265	08/17/82	Blanchard	357	23	04/14/80
	4,366,495	12/28/82	Goodman et al	357	23	08/06/79
	4,376,286	03/08/83	Lidow et al.	357	23	02/09/81
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation YES NO
	EP 0 053 854 B1	16.06.82	EPO	H01L	29/06	x
	GB 2 089 118 A	16.02.82	UK	H01L	29/78	x
	EP 0 069 429 A2	12.01.83	EPO	H01L	29/78	x
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	1977	Richard F. David: "Computerized Thermal Analysis of Hybrid Circuits" 27th Electronics Components Conference, May 16-18 1977 (p 324-332)
EXAMINER	DATE CONSIDERED 8/24/04	

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Docket Number (Optional)

068758.0102

Application Number

09786,822

10/633,144

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
PB	4,404,575	09/13/83	Nishizawa	357	22	05/03/82
	4,417,385	11/29/83	Temple	29	571	09/09/82
	4,561,003	12/24/85	Tihanyi et al.	357	23.4	04/13/84
	4,593,302	06/03/86	Lidow et al.	357	23.4	08/18/80
	4,748,103	05/31/88	Hollinger	430	314	03/21/66
	4,754,310	06/28/88	Coc	357	13	12/04/84
	4,775,881	10/04/88	Ploss et al.	357	30	02/13/87
	4,777,149	10/11/88	Tanabe et al.	437	142	12/22/87
	4,895,810	01/23/90	Meyers et al.	431	41	05/17/88
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation YES NO
	EP 0 772 244 A1	07.05.97	EPO	H01L	29/78	x
	DE 196 04 043 A1	5.2.96	Germany	H01L	29/78	x
	WO 97/29518	14.08.97	PCT	H01L	29/78	x
	DE 196 04 044 A1	5.2.97	Germany	H01L	29/78	x
	WO 97/35346	25.09.97	PCT	H01L	29/78	x
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	DE 197 30 759 C1	17.7.97	Germany	H01L	29/78	x
	WO 99/04437	28.01.99	PCT	H01L	29/78	x
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Docket Number (Optional)

068758.0102

Application Number

09/286,022

10/633,041

Applicant Deboy et al.

Filing Date 04/22/99

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
P	4,914,058	04/03/90	Blanchard	437	203	12/29/87	
	4,926,226	05/15/90	Heremans et al.	357	27	09/06/88	
	4,941,026	07/10/90	Temple	357	23.4	08/26/88	
	4,974,059	11/27/90	Kinzer	357	23.4	08/28/89	
	4,975,782	12/04/90	Bauer	357	38	02/22/89	
	4,994,871	02/19/91	Chang et al.	357	23.4	12/02/88	
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	WO99/36961	22.07.99	PCT	H01L	23/48		x
	DE 197 36 981C2	25.8.97	Germany	H01L	29/78		x
	EP 0 939 446 A1	01/09/99	EPO	H01L	29/08		x
	WO 00/14807	16.03.00	PCT	H01L	29/78		x
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Docket Number (Optional)

068758.0102

Application Number

09786,022

107633044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE	
PP	5,126,807	06/30/92	Baba et al.	357	23.4	06/12/91	
	5,182,234	01/26/93	Meyer	437	233	07/26/91	
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	5,231,474	07/27/93	Hollinger	257	355	07/17/92	
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	5,438,215	08/01/95	Tihyani	257	401	03/25/94	
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WO 00/02250	13.01.00	PCT	H01L	29/10		x	
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Docket Number (Optional)

068758.0102

Application Number

09/286,027

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
<i>JP</i>	5,473,180	12/05/95	Ludikhuizen	257	336	07/11/94
	5,559,353	09/24/96	Risch et al.	257	334	11/01/94
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	5,747,831	05/05/98	Loose et al.	257	77	
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	Translation YES NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)



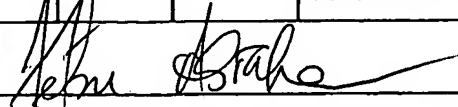
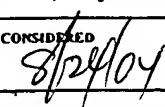
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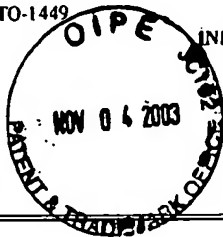
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Sheet 6 of 8

Form PTO-1449				Docka Number (Optional)		Application Number			
 <p>INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)</p>				068758.0102		09786,022 10/633,044			
				Applicant Deboy et al.					
				Filing Date 04/22/99		Group Art Unit:			
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	IEEE	1984	Chenming Hu, Min-Hwa Chi, Vikram M. Patel: "Optimum Designs of Power MOSFET's" (p 1693-1700)						
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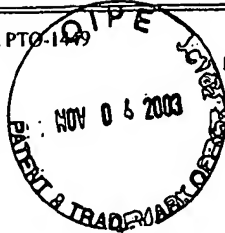
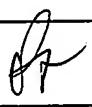

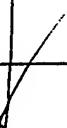
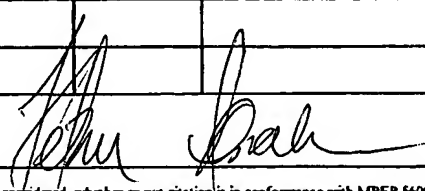
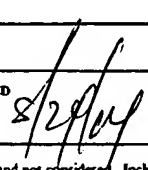
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		1991	Article by Xing-Bi Chen presented at 2 nd German-Chinese Electronics Week Congress, Shanghai, China.
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		May 1998	Article, "Siemens Introduces new Generation of High-Voltage MOSFET Technology"
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						Applicant Deboy et al.			
						Filing Date 04/22/99		Group Art Unit:	
U.S. PATENT DOCUMENTS									
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